Transport in adatom-decorated graphene

Erik Henriksen Chandni U & J.P. Eisenstein





Jamie Elias (and EAH)



Outline

I. Motivation

topological physics from adatoms on graphene

- Indium atoms on graphene (Caltech) experimental apparatus for *in situ* deposition results
- III. 5d atoms on graphene (Wash. U.)
 2nd generation apparatus initial findings







Wang et al., Science 342, 614 (2013)



Deposition of *K* atoms



Chen et al., Nature Phys 4, 377 (2008)

also Yan & Fuhrer, PRL 107, 206601 (2011)

Adsorption of molecules



Schedin et al., Nature Materials 6, 652 (2007)

Chemical functionalization



fluorinated and fluoro-graphene

Nair *et al.*, Small **6**, 2877 (2010) Jeon *et al.*, ACS Nano **5**, 1042 (2011) Hong *et al.*, PRB **83**, 085410 (2011)





graphane

Sofo *et al.*, Phys. Rev. B **75**, 153401 (2007) Elias *et al.*, Science **323**, 610 (2009)



Graphene topological insulator

Kane & Mele, Phys. Rev. Lett. 95, 226801 (2005)

$$H = \hbar \tilde{c} \begin{pmatrix} 0 & k_x - ik_y \\ k_x + ik_y & 0 \end{pmatrix} \qquad \qquad H = \hbar \tilde{c} \begin{pmatrix} \Delta_{SO} & k_x - ik_y \\ k_x + ik_y & -\Delta_{SO} \end{pmatrix}$$



Graphene topological insulator

Kane & Mele, Phys. Rev. Lett. 95, 226801 (2005)



Topological insulators

2D







Hsieh et al., Nature 452, 970 (2008)

Graphene topological insulator

Weeks et al., PRX 1, 021001 (2011)





indium

7 meV gap

thallium

21 meV gap

Graphene topological insulator

Weeks et al., PRX 1, 021001 (2011) 0.3 2 Hu et al., PRL 109, 266801 (2012) Os $0.2 \Delta_{SO}$ (eV) Cu-Os Energy (eV) 0 4_{SO} 0.1 -1 -2 0 ר M K Γ 0 2 3 4 5 6 7 Γ 1 Coverage (%)

with 5*d* atoms e.g. osmium

Outline

I. Motivation

topological physics from adatoms on graphene

II. Indium atoms on graphene experimental apparatus for *in situ* deposition results

III. 5d atoms on graphene2nd generation apparatusinitial findings

In situ evaporation



Evaporation sources















Magnetoresistance



Magnetoresistance



2

Weak localization



Weak localization



modified fit based on McCann et al., PRL 97, 146805 (2006):

$$\Delta \sigma = \frac{e^2}{\pi h} \left[F(\frac{B}{B_{\phi}}) - F(\frac{B}{B_{\phi} + 2B_i}) - 2F(\frac{B}{B_{\phi} + B_i}) \right]$$
$$F(z) = \ln(z) + \psi(\frac{1}{2} + \frac{1}{z}), \quad B_{\phi,i} = \frac{\hbar}{4De} \tau_{\phi,i}^{-1}$$

limit to fit: $l_{\mu}^2 < l_B^2$



Weak localization

modified fit based on McCann et al., PRL 97, 146805 (2006):

$$\Delta \sigma = \frac{e^2}{\pi h} \left[F(\frac{B}{B_{\phi}}) - F(\frac{B}{B_{\phi} + 2B_i}) - 2F(\frac{B}{B_{\phi} + B_i}) \right]$$
$$F(z) = \ln(z) + \psi(\frac{1}{2} + \frac{1}{z}), \quad B_{\phi,i} = \frac{\hbar}{4De} \tau_{\phi,i}^{-1}$$
$$limit \text{ to fit: } l_{\mu}^2 < l_B^2$$





Outline

I. Motivation

topological physics from adatoms on graphene

- Indium atoms on graphene experimental apparatus for *in situ* deposition results
- III. 5d atoms on graphene 2nd generation apparatus initial findings

2nd generation evaporator







Osmium evaporation sources



tungsten

annealed tungsten

coated with osmium

g-BN devices











The end. *Thank you!*

Measurements: Chandni U, EAH, J.P. Eisenstein at Caltech arxiv: 1503.04191 Jamie Elias, EAH at Washington University

Many thanks to:

Caltech

Jason Alicea Keith Schwab Johannes Pollanen Debaleena Nandi KC Fong Ari Weinstein <u>Washington University</u> Jordan Russell Nero Zhou Todd Hardt

<u>Columbia University</u> Cory Dean

<u>Bard College</u> Paul Cadden-Zimansky